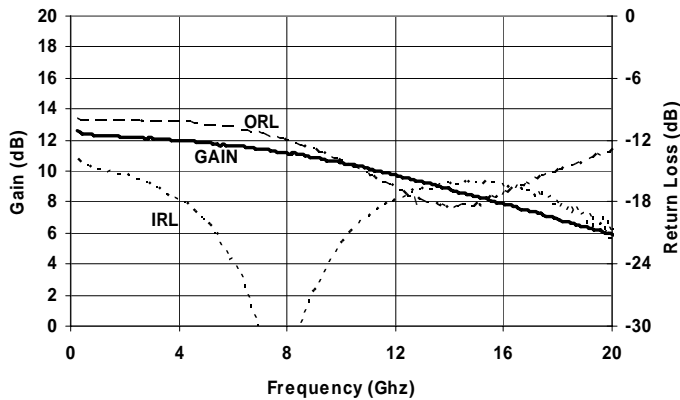




Product Description

Sirenza Microdevices' SUF-2000 is a monolithically matched broadband high IP3 gain block covering 0.05-10 GHz. This pHEMT FET-based amplifier uses a patented self-bias Darlington topology featuring a gain and temperature compensating active bias network that operates from a single 5V supply. It offers efficient, cascadable performance in a compact 0.88 x 0.86 mm² die. It is well-suited for RF, LO, and IF driver applications.

Gain & Return Loss vs. Frequency
(GSG Probe Data)



Preliminary

SUF-2000

0.2-10 GHz, Cascadable pHEMT MMIC Amplifier

Product Features

- Broadband Performance
- High Gain = 12.0 dB @ 6 GHz
- P1dB = 16 dBm @ 6 GHz
- Low-noise, Efficient Gain Block
- 3.3V Operation, No Dropping Resistor
- Low Gain Variation vs. Temperature
- Patented Thermal Design
- Patented Self-Bias Darlington Circuit

Applications

- Broadband Communications
- Test Instrumentation
- Military & Space
- LO and IF Mixer Applications
- High IP3 RF Driver Applications

Symbol	Parameters	Units	Frequency	Min.	Typ.	Max.
G _p	Small Signal Power Gain	dB	2 GHz		12.0	
			6 GHz		11.5	
			10 GHz		11.0	
P1dB	Output Power at 1dB Compression	dBm	2 GHz		16.0	
			6 GHz		16.0	
			10 GHz		15.5	
OIP3	Output Third Order Intercept Point	dBm	2 GHz		33.0	
			6 GHz		30.0	
			10 GHz		27.0	
NF	Noise Figure	dB	2 GHz		3.6	
			6 GHz		3.6	
			10 GHz		4.6	
IRL	Input Return Loss	dB	2 GHz		-16.0	
			6 GHz		-24.0	
			10 GHz		-22.0	
ORL	Output Return Loss	dB	2 GHz		-10.0	
			6 GHz		-11.0	
			10 GHz		-15.0	
Isol	Reverse Isolation	dB	2 GHz		-18.0	
			6 GHz		-17.0	
			10 GHz		-16.0	
V _D	Device Operating Voltage	V			3.3	
I _D	Device Operating Current	mA			71	
ΔG/ΔT	Device Gain Temperature Coefficient	dB/°C			-0.01	
R _{th, j-l}	Thermal Resistance (junction-to-backside)	°C/W			256	

Test Conditions: V_S = 3.3V, I_D = 71mA OIP3 Tone Spacing = 1MHz, P_{out} per tone = 0 dBm
Z_S = Z_L = 50 Ohms. GSG Probe Data With Bias Tees

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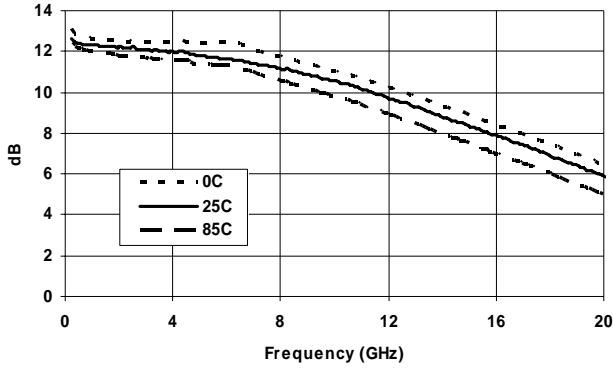
Phone: (800) SMI-MMIC

<http://www.sirenza.com>

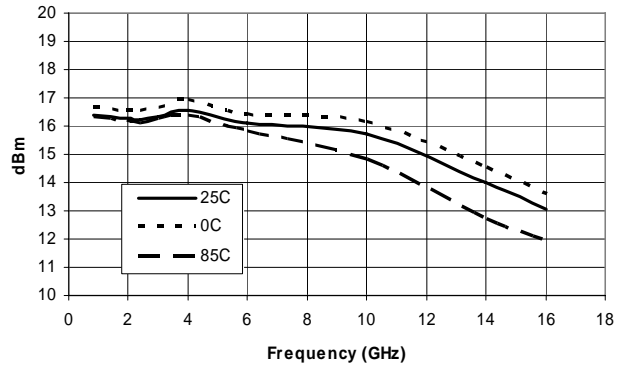


Typical Performance (GSG Probe Data)

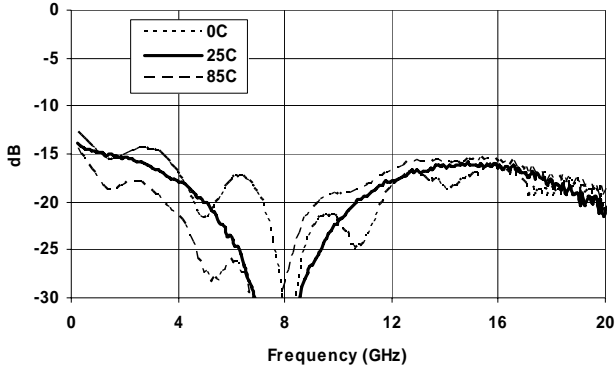
S21 vs. Frequency



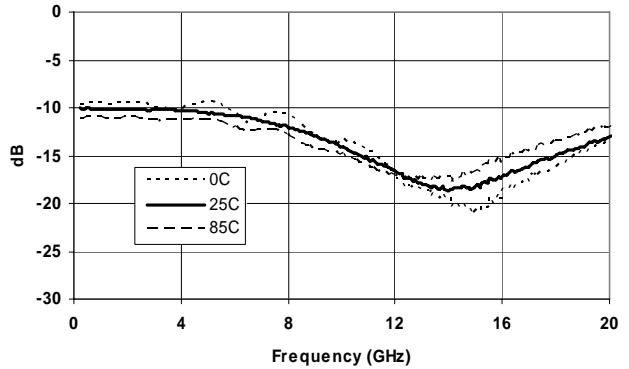
P1dB vs. Frequency



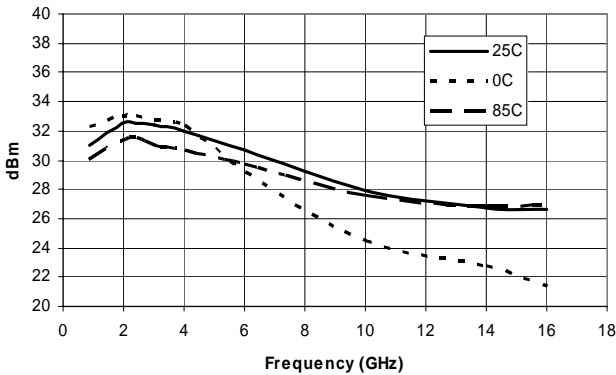
S11 vs. Frequency



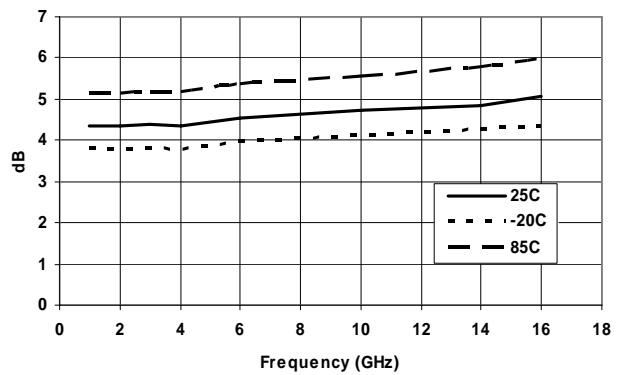
S22 vs. Frequency



OIP3 vs. Frequency



Noise Figure vs. Frequency



Typical Performance (GSG Probe Data)

Freq (GHz)	V _D (V)	Current (mA)	Gain (dB)	P1dB (dBm)	OIP3 (dBm)	S11 (dB)	S22 (dB)	NF (dB)
0.2	3.3	71	12.5			-14.0	-10.0	
0.5	3.3	71	12.5			-14.0	-10.0	
0.85	3.3	71	12.5	16.5	31.0	-15.0	-10.0	3.7
2	3.3	71	12.0	16.0	33.0	-16.0	-10.0	3.6
4	3.3	71	12.0	16.5	32.0	-18.0	-10.5	3.8
6	3.3	71	11.5	16.0	30.0	-24.0	-11.0	3.6
10	3.3	71	11.0	15.5	27.0	-22.0	-15.0	4.6
16	3.3	71	8.0	13.0	25.0	-16.0	-17.0	5.4

Test Conditions: GSG Probe Data With Bias Tees, OIP3 Tone Spacing = 1MHz, Pout per tone = 0 dBm, 25°C

Parameter	Absolute Limit
Max Device Current (I _D)	80mA
Max Device Voltage (V _D)	3.6V
Max RF Input Power	10dBm
Max Dissipated Power	288mW
Max Junction Temperature (T _J)	150C
Operating Temperature Range (T _L)	-40 to +85C
Max Storage Temp.	-65 to 150C

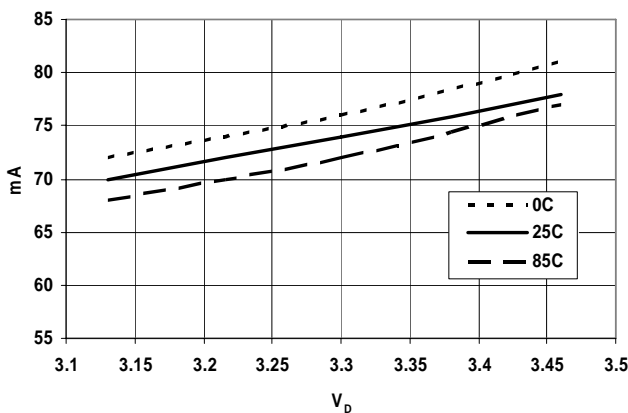
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

$$I_D V_D < (T_J - T_L) / R_{TH}, \text{ j-l } T_L = \text{Backside of die}$$

Current Variation vs. Temperature

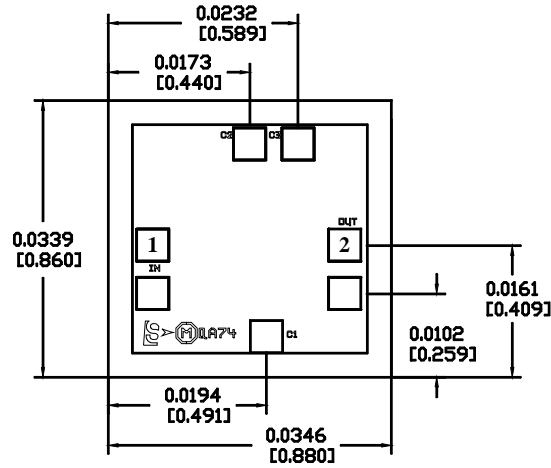
Current vs. Voltage



ELECTROSTATIC SENSITIVE DEVICE

Appropriate precautions in handling, packaging and testing devices must be observed.

Pad Description



Pad #	Function	Description
1	RF _{IN}	This pad is DC coupled and matched to 50 Ohms. An external DC block is required.
2	RF _{OUT} / Bias	This pad is DC coupled and matched to 50 Ohms. Bias is applied through this pad.
Die Bottom	GND	Die bottom must be connected to RF/DC ground using silver-filled conductive epoxy.

- Notes:
1. All Dimensions in Inches [Millimeters].
 2. No connection required for unlabeled bond pads.
 3. Die Thickness is 0.004 (0.100).
 4. Typical bond pad is 0.004 (0.100) square.
 5. Backside metalization: Gold.
 6. Backside is Ground.
 7. Bond pad metalization: Gold.

Device Assembly

